

## SILICON NPN SWITCHING TRANSISTORS

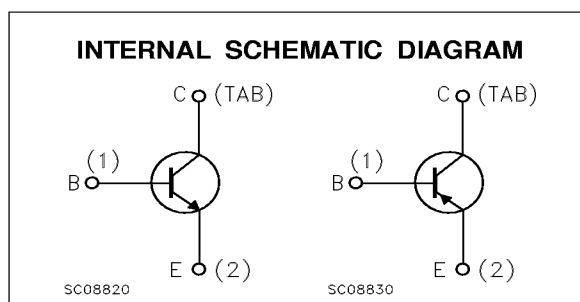
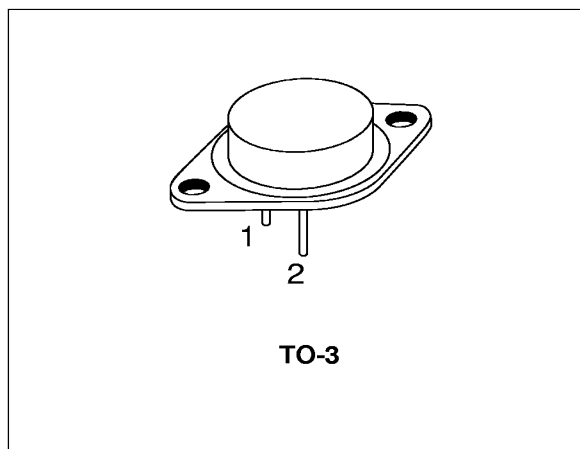
- SGS-THOMSON PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- HIGH DC CURRENT GAIN

### APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

### DESCRIPTION

The BDW51C is a silicon epitaxial-base NPN transistor in Jedec TO-3 metal case. It is intended for use in power linear and switching applications. The complementary PNP is the BDW52C.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	PNP	
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	<b>BDW51C</b>		V
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	<b>BDW52C</b>		
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	100		V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	5		V
$I_C$	Collector Current	15		A
$I_{CM}$	Collector Peak Current (repetitive)	20		A
$I_B$	Base Current	7		A
$P_{tot}$	Total Dissipation at $T_c = 25^\circ\text{C}$	125		W
$T_{stg}$	Storage Temperature	-65 to 200		$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	200		$^\circ\text{C}$

For PNP types voltage and current values are negative.

## BDW51C / BDW52C

### THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.4	$^{\circ}C/W$
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### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = 100 V$ $V_{CB} = 100 V$ $T_{case} = 150^{\circ}C$			500 5	$\mu A$ mA
$I_{CEO}$	Collector Cut-off Current ( $I_B = 0$ )	$V_{CE} = 50 V$			1	mA
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 5 V$			2	mA
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage	$I_C = 100 mA$	100			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 5 A$ $I_B = 0.5 A$ $I_C = 10 A$ $I_B = 2.5 A$			1 3	V
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = 10 A$ $I_B = 2.5 A$			2.5	V V
$V_{BE*}$	Base-Emitter Voltage	$I_C = 5 A$ $V_{CE} = 4 V$			1.5	V
$h_{FE*}$	DC Current Gain	$I_C = 5 A$ $V_{CE} = 4 V$ $I_C = 10 A$ $V_{CE} = 4 V$	20 5		150	
$f_T$	Transition frequency	$I_C = 1 A$ $V_{CE} = 4 V$	3			MHz

\* Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %  
For PNP types voltage and current values are negative.

**TO-3 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193

